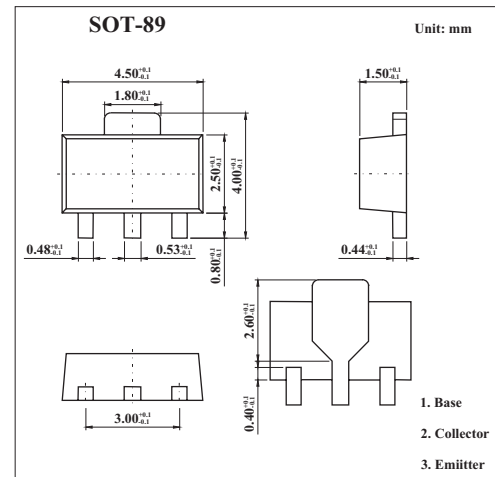


Medium Power Transistor

FCX491

■ Features

- 60 Volt V_{CEO} .
- 1 Amp continuous current.
- P_{tot} = 1 Watt.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	5	V
Peak pulse current	I_c	1	A
Continuous collector current	I_{CM}	2	A
Power dissipation	P_{tot}	1	W
Operating and storage temperature range	T_j, T_{stg}	-65 to +150	$^\circ\text{C}$

FCX491

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Breakdown Voltages	V _{(BR)CBO}	I _C =100μA	80			V
Breakdown Voltages	V _{CEO(sus)}	I _C =10mA	60			V
Breakdown Voltages	V _{(BR)EBO}	I _E =100μA	5			V
Collector-base cut-off current	I _{CBO}	V _{CB} =60V			100	nA
	I _{CES}	V _{CE} =60V			100	nA
Emitter-base current	I _{EBO}	V _{EB} =4V			100	nA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =500mA, I _B =50mA I _C =1A, I _B =100mA			0.25 0.5	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =1A, I _B =100mA			1.1	V
Base-emitter ON voltage *	V _{BE(on)}	I _C =1A, V _{CE} =5V			1.0	V
Static Forward Current Transfer Ratio *	h _{FE}	I _C =1mA, V _{CE} =5V	100			
		I _C =500mA, V _{CE} =5V*	100		300	
		I _C =1A, V _{CE} =5V*	80			
		I _C =2A, V _{CE} =5V*	30			
Transitional frequency	f _T	I _C =50mA, V _{CE} =10V f=100MHz	150			MHz
Output capacitance	C _{obo}	V _{CB} =10V, f=1MHz			10	pF

* Pulse test: t_p = 300 μs; d ≤ 0.02.

■ Marking

Marking	N1
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